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Kind regards,

Team Nexperia



# PMN40ENE

30 V, N-channel Trench MOSFET

24 May 2016

Product data sheet

## 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT457 (SC-74) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

## 2. Features and benefits

- Trench MOSFET technology
- Logic-level compatible
- Very fast switching
- Enhanced power dissipation capability of 1240 mW
- ElectroStatic Discharge (ESD) protection > 1 kV HBM

## 3. Applications

- LED driver
- Power management
- Low-side loadswitch
- Switching circuits

## 4. Quick reference data

Table 1. Quick reference data

| Symbol                        | Parameter                        | Conditions                                                                      |     | Min | Typ | Max | Unit       |
|-------------------------------|----------------------------------|---------------------------------------------------------------------------------|-----|-----|-----|-----|------------|
| $V_{DS}$                      | drain-source voltage             | $T_j = 25\text{ }^{\circ}\text{C}$                                              |     | -   | -   | 30  | V          |
| $V_{GS}$                      | gate-source voltage              |                                                                                 |     | -20 | -   | 20  | V          |
| $I_D$                         | drain current                    | $V_{GS} = 10\text{ V}; T_{amb} = 25\text{ }^{\circ}\text{C}; t \leq 5\text{ s}$ | [1] | -   | -   | 5.7 | A          |
| <b>Static characteristics</b> |                                  |                                                                                 |     |     |     |     |            |
| $R_{DS(on)}$                  | drain-source on-state resistance | $V_{GS} = 10\text{ V}; I_D = 4.5\text{ A}; T_j = 25\text{ }^{\circ}\text{C}$    |     | -   | 30  | 38  | m $\Omega$ |

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

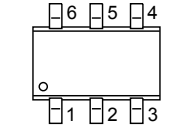
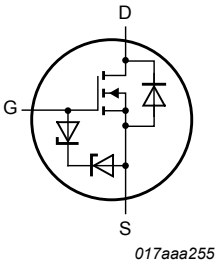


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5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline                                                                                      | Graphic symbol                                                                      |
|-----|--------|-------------|---------------------------------------------------------------------------------------------------------|-------------------------------------------------------------------------------------|
| 1   | D      | drain       |  <p>TSOP6 (SOT457)</p> |  |
| 2   | D      | drain       |                                                                                                         |                                                                                     |
| 3   | G      | gate        |                                                                                                         |                                                                                     |
| 4   | S      | source      |                                                                                                         |                                                                                     |
| 5   | D      | drain       |                                                                                                         |                                                                                     |
| 6   | D      | drain       |                                                                                                         |                                                                                     |

6. Ordering information

Table 3. Ordering information

| Type number | Package |                                                  |         |
|-------------|---------|--------------------------------------------------|---------|
|             | Name    | Description                                      | Version |
| PMN40ENE    | TSOP6   | plastic surface-mounted package (TSOP6); 6 leads | SOT457  |

7. Marking

Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| PMN40ENE    | H4           |

## 8. Limiting values

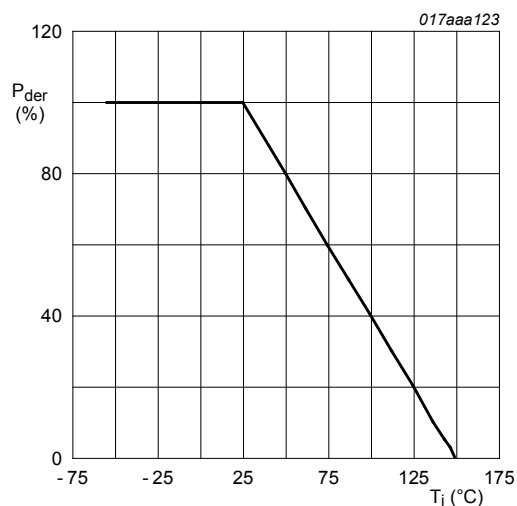
**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol                    | Parameter               | Conditions                                                     |     | Min | Max  | Unit |
|---------------------------|-------------------------|----------------------------------------------------------------|-----|-----|------|------|
| V <sub>DS</sub>           | drain-source voltage    | T <sub>j</sub> = 25 °C                                         |     | -   | 30   | V    |
| V <sub>GS</sub>           | gate-source voltage     |                                                                |     | -20 | 20   | V    |
| I <sub>D</sub>            | drain current           | V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C; t ≤ 5 s      | [1] | -   | 5.7  | A    |
|                           |                         | V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C               | [1] | -   | 4.5  | A    |
|                           |                         | V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 100 °C              | [1] | -   | 2.9  | A    |
| I <sub>DM</sub>           | peak drain current      | T <sub>amb</sub> = 25 °C; single pulse; t <sub>p</sub> ≤ 10 μs |     | -   | 18   | A    |
| P <sub>tot</sub>          | total power dissipation | T <sub>amb</sub> = 25 °C                                       | [2] | -   | 530  | mW   |
|                           |                         |                                                                | [1] | -   | 1.24 | W    |
|                           |                         | T <sub>sp</sub> = 25 °C                                        |     | -   | 4.46 | W    |
| T <sub>j</sub>            | junction temperature    |                                                                |     | -55 | 150  | °C   |
| T <sub>amb</sub>          | ambient temperature     |                                                                |     | -55 | 150  | °C   |
| T <sub>stg</sub>          | storage temperature     |                                                                |     | -65 | 150  | °C   |
| <b>Source-drain diode</b> |                         |                                                                |     |     |      |      |
| I <sub>S</sub>            | source current          | T <sub>amb</sub> = 25 °C                                       | [1] | -   | 1.2  | A    |

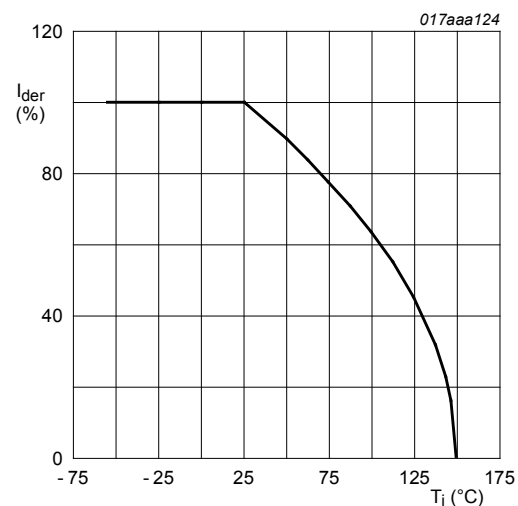
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



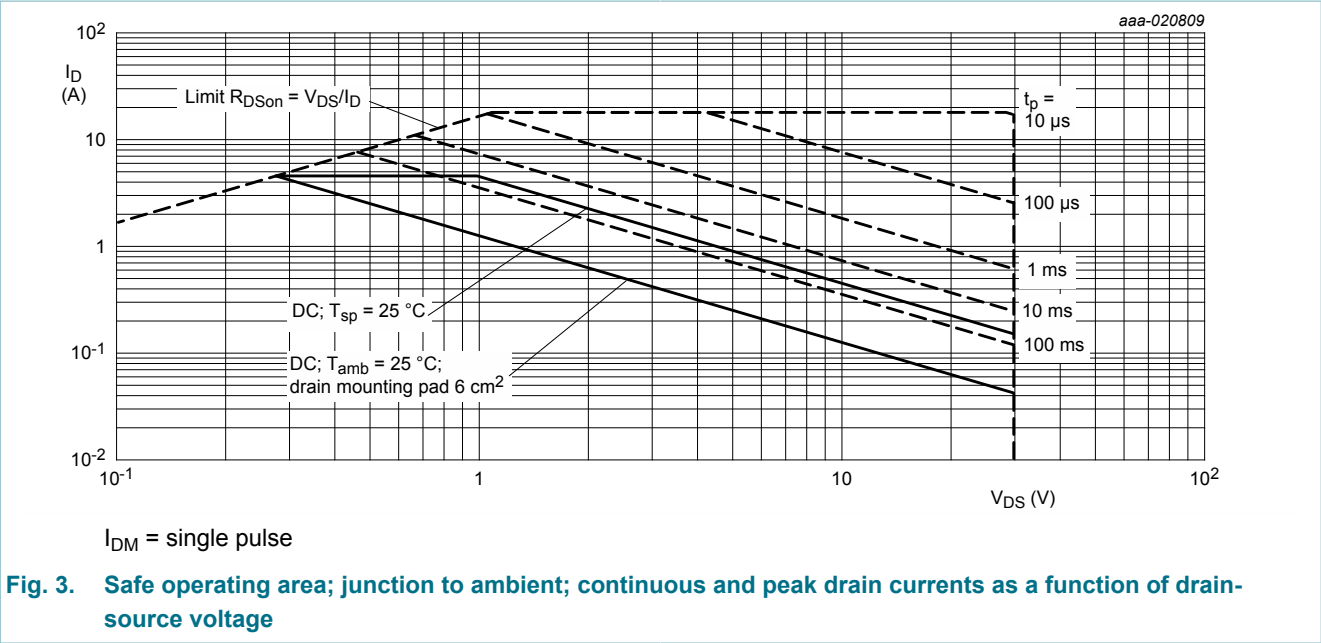
**Fig. 1. Normalized total power dissipation as a function of junction temperature**

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}\text{C})}} \times 100 \%$$



**Fig. 2. Normalized continuous drain current as a function of junction temperature**

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}\text{C})}} \times 100 \%$$



9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol         | Parameter                                        | Conditions                |     | Min | Typ | Max | Unit |
|----------------|--------------------------------------------------|---------------------------|-----|-----|-----|-----|------|
| $R_{th(j-a)}$  | thermal resistance from junction to ambient      | in free air               | [1] | -   | 205 | 235 | K/W  |
|                |                                                  |                           | [2] | -   | 88  | 101 | K/W  |
|                |                                                  | in free air; $t \leq 5$ s | [2] | -   | 55  | 63  | K/W  |
| $R_{th(j-sp)}$ | thermal resistance from junction to solder point |                           |     | -   | 24  | 28  | K/W  |

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.  
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

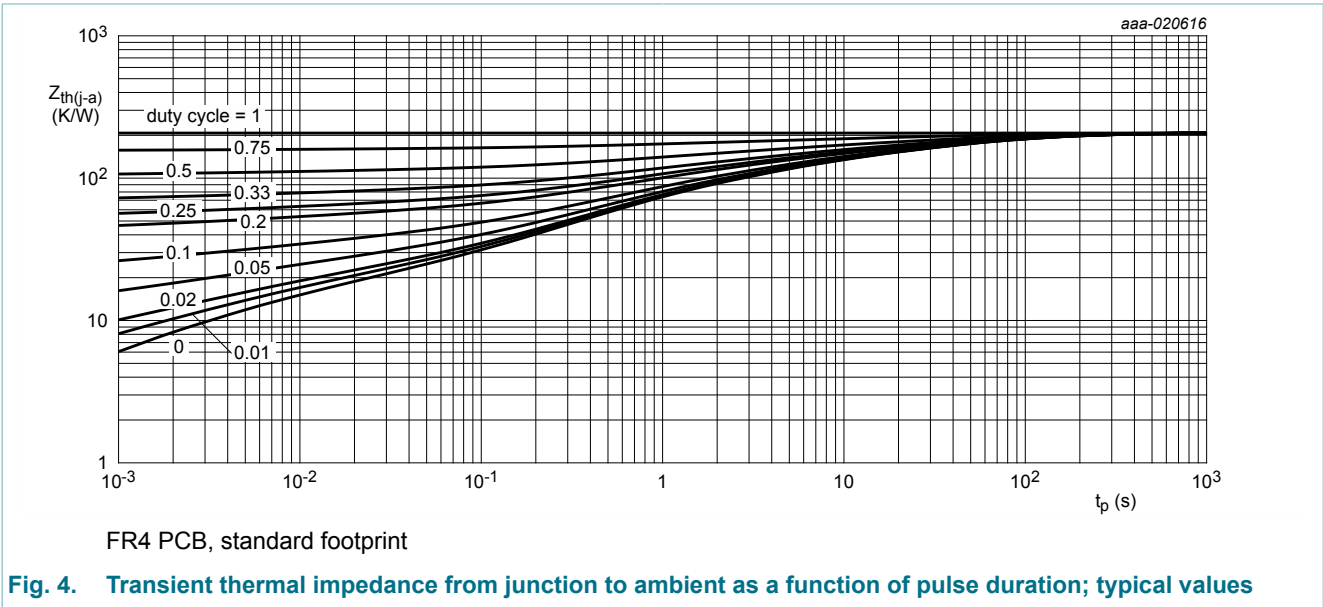
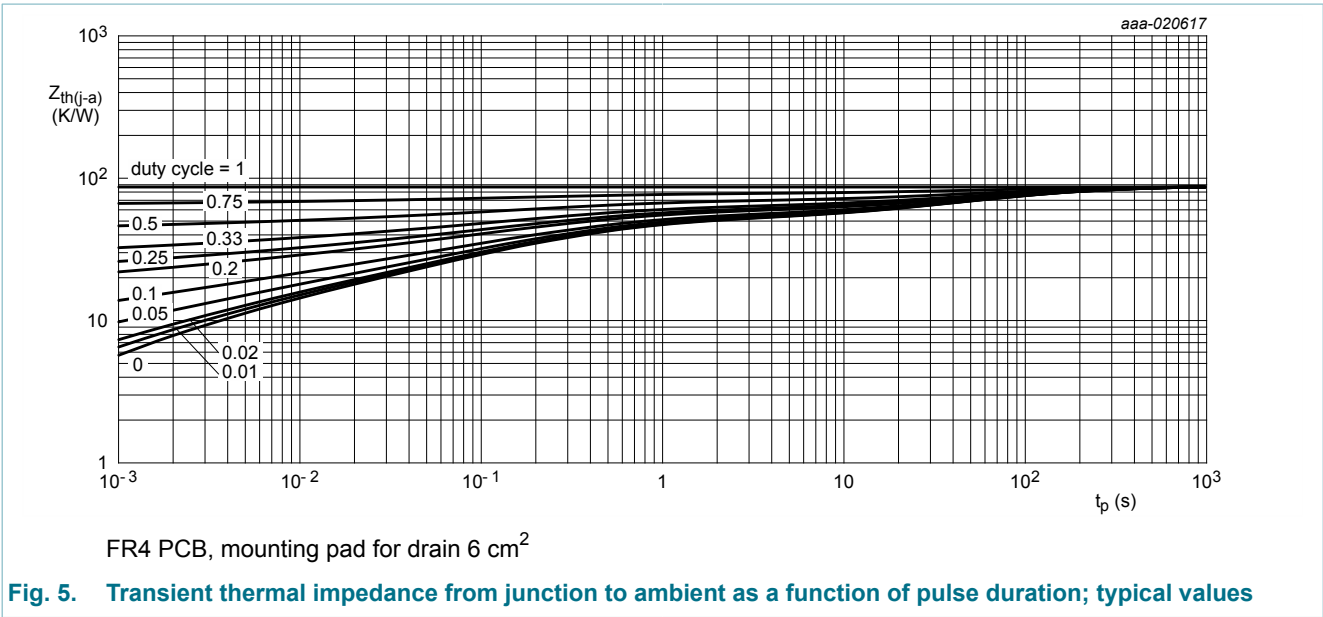


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



## 10. Characteristics

Table 7. Characteristics

| Symbol                  | Parameter                        | Conditions                                                                                                                |  | Min | Typ  | Max  | Unit |
|-------------------------|----------------------------------|---------------------------------------------------------------------------------------------------------------------------|--|-----|------|------|------|
| Static characteristics  |                                  |                                                                                                                           |  |     |      |      |      |
| V <sub>(BR)DSS</sub>    | drain-source breakdown voltage   | I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C                                                    |  | 30  | -    | -    | V    |
| V <sub>GSth</sub>       | gate-source threshold voltage    | I <sub>D</sub> = 250 μA; V <sub>DS</sub> =V <sub>GS</sub> ; T <sub>j</sub> = 25 °C                                        |  | 1   | 1.4  | 2    | V    |
| I <sub>DSS</sub>        | drain leakage current            | V <sub>DS</sub> = 30 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C                                                     |  | -   | -    | 1    | μA   |
| I <sub>GSS</sub>        | gate leakage current             | V <sub>GS</sub> = 16 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C                                                     |  | -   | -    | 10   | μA   |
|                         |                                  | V <sub>GS</sub> = -16 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C                                                    |  | -   | -    | -10  | μA   |
|                         |                                  | V <sub>GS</sub> = 10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C                                                     |  | -   | -    | 1    | μA   |
|                         |                                  | V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C                                                    |  | -   | -    | -1   | μA   |
|                         |                                  | V <sub>GS</sub> = 4.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C                                                    |  | -   | -    | 200  | nA   |
|                         |                                  | V <sub>GS</sub> = -4.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C                                                   |  | -   | -    | -200 | nA   |
| R <sub>DSon</sub>       | drain-source on-state resistance | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 4.5 A; T <sub>j</sub> = 25 °C                                                    |  | -   | 30   | 38   | mΩ   |
|                         |                                  | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 4.5 A; T <sub>j</sub> = 150 °C                                                   |  | -   | 47   | 60   | mΩ   |
|                         |                                  | V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 3.3 A; T <sub>j</sub> = 25 °C                                                   |  | -   | 44   | 70   | mΩ   |
| g <sub>fs</sub>         | forward transconductance         | V <sub>DS</sub> = 10 V; I <sub>D</sub> = 2 A; T <sub>j</sub> = 25 °C                                                      |  | -   | 10.7 | -    | S    |
| R <sub>G</sub>          | gate resistance                  | T <sub>j</sub> = 25 °C; f = 1 MHz                                                                                         |  | -   | 0.5  | -    | Ω    |
| Dynamic characteristics |                                  |                                                                                                                           |  |     |      |      |      |
| Q <sub>G(tot)</sub>     | total gate charge                | V <sub>DS</sub> = 15 V; I <sub>D</sub> = 3.2 A; V <sub>GS</sub> = 10 V; T <sub>j</sub> = 25 °C                            |  | -   | 5.6  | 11   | nC   |
| Q <sub>GS</sub>         | gate-source charge               |                                                                                                                           |  | -   | 0.76 | -    | nC   |
| Q <sub>GD</sub>         | gate-drain charge                |                                                                                                                           |  | -   | 1.1  | -    | nC   |
| C <sub>iss</sub>        | input capacitance                | V <sub>DS</sub> = 15 V; f = 1 MHz; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C                                          |  | -   | 294  | -    | pF   |
| C <sub>oss</sub>        | output capacitance               |                                                                                                                           |  | -   | 42   | -    | pF   |
| C <sub>rss</sub>        | reverse transfer capacitance     |                                                                                                                           |  | -   | 33   | -    | pF   |
| t <sub>d(on)</sub>      | turn-on delay time               | V <sub>DS</sub> = 15 V; I <sub>D</sub> = 3.2 A; V <sub>GS</sub> = 10 V; R <sub>G(ext)</sub> = 6 Ω; T <sub>j</sub> = 25 °C |  | -   | 4.6  | -    | ns   |
| t <sub>r</sub>          | rise time                        |                                                                                                                           |  | -   | 14.7 | -    | ns   |
| t <sub>d(off)</sub>     | turn-off delay time              |                                                                                                                           |  | -   | 9.1  | -    | ns   |
| t <sub>f</sub>          | fall time                        |                                                                                                                           |  | -   | 3    | -    | ns   |
| Source-drain diode      |                                  |                                                                                                                           |  |     |      |      |      |
| V <sub>SD</sub>         | source-drain voltage             | I <sub>S</sub> = 1.2 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C                                                     |  | -   | 0.8  | 1.2  | V    |



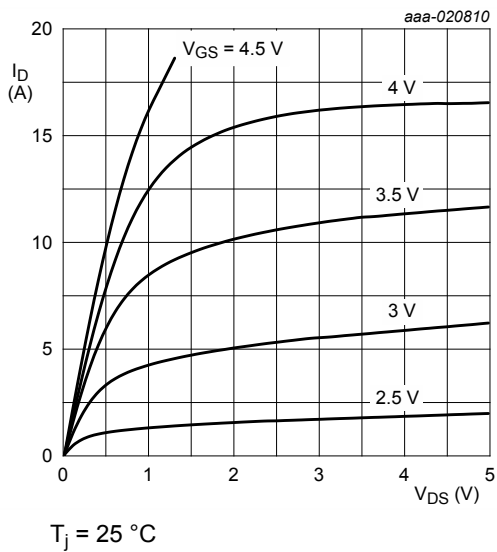


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

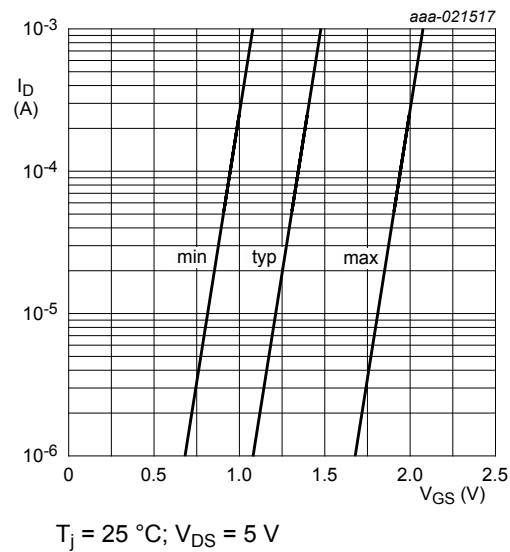


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

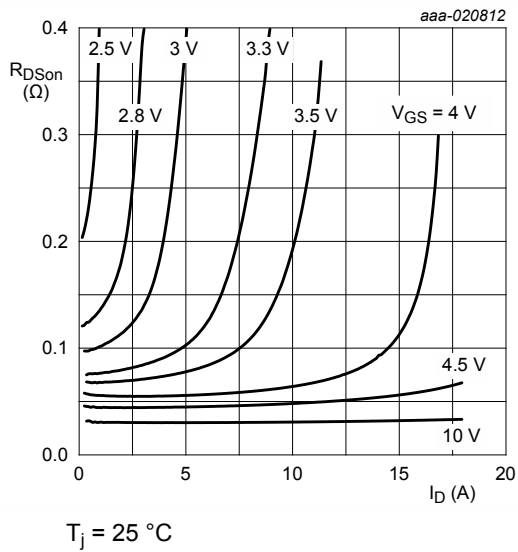


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

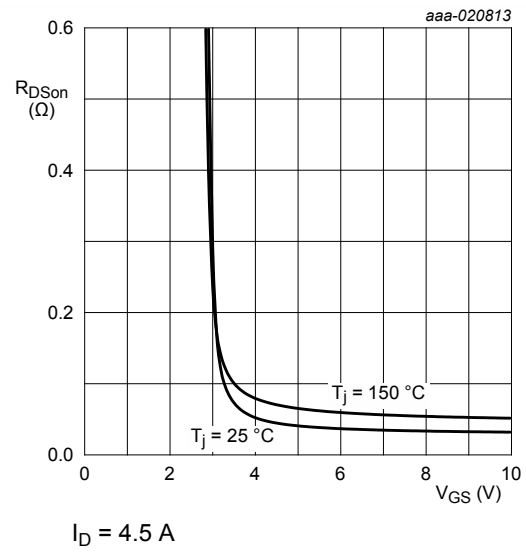


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

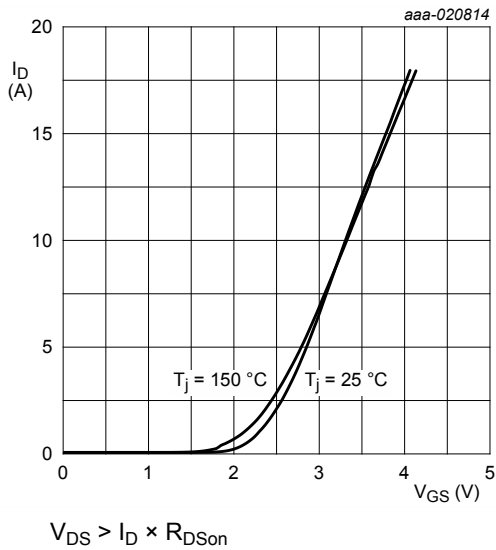


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

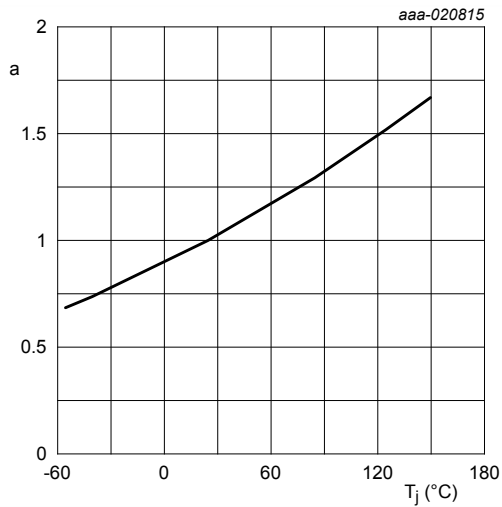


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}\text{C})}}$$

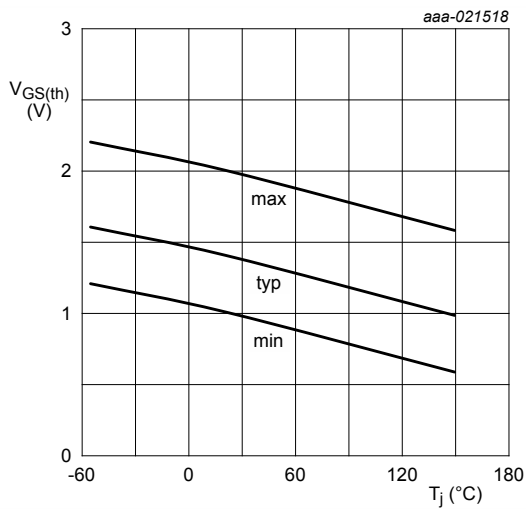


Fig. 12. Gate-source threshold voltage as a function of junction temperature

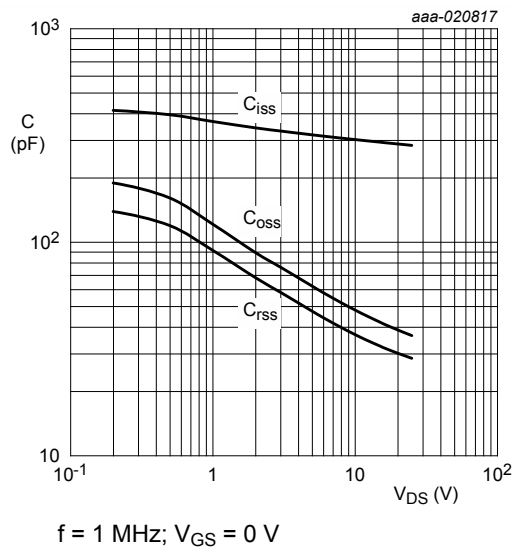


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

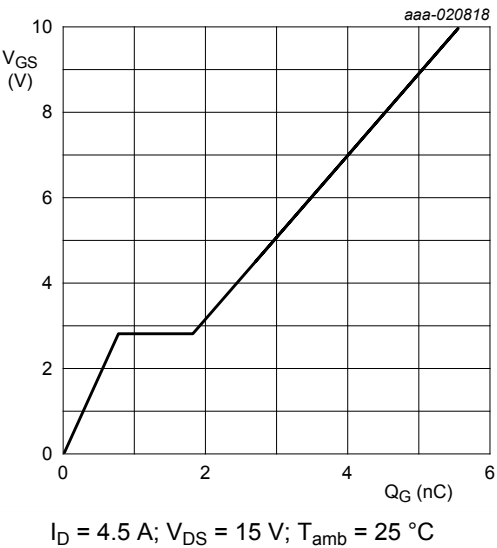


Fig. 14. Gate-source voltage as a function of gate charge; typical values

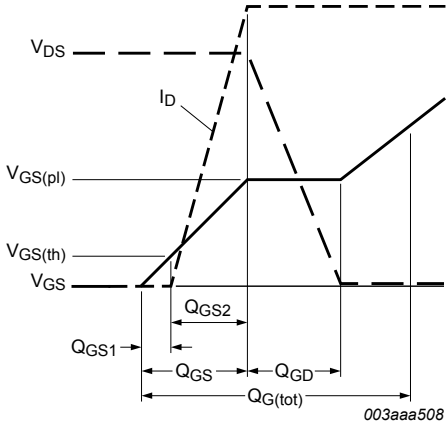
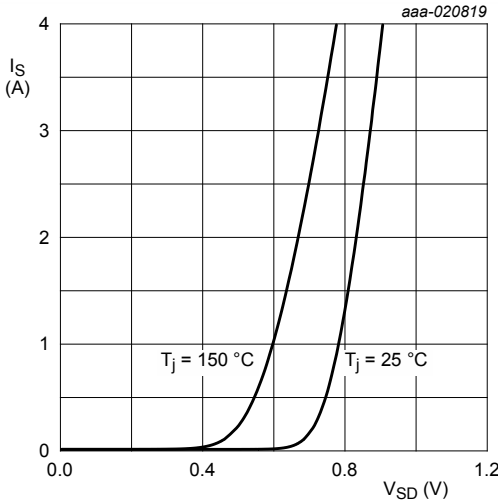


Fig. 15. MOSFET transistor: Gate charge waveform definitions



$V_{GS} = 0\text{ V}$

Fig. 16. Source current as a function of source-drain voltage; typical values

## 11. Test information

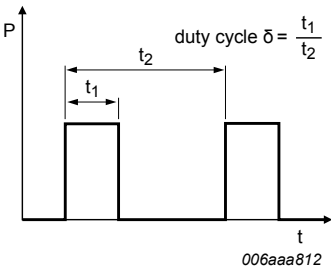
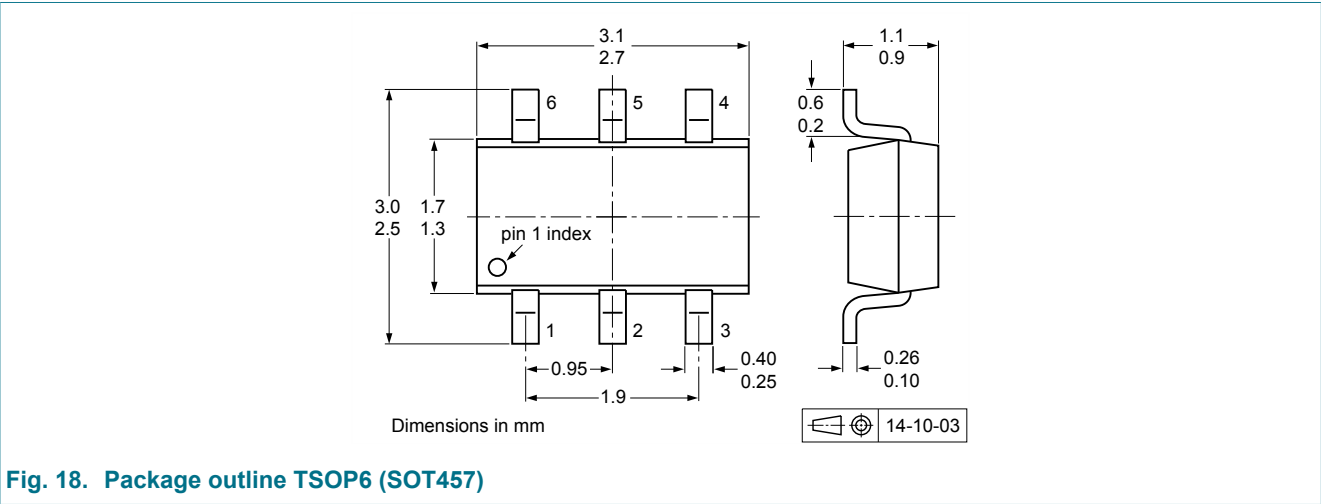
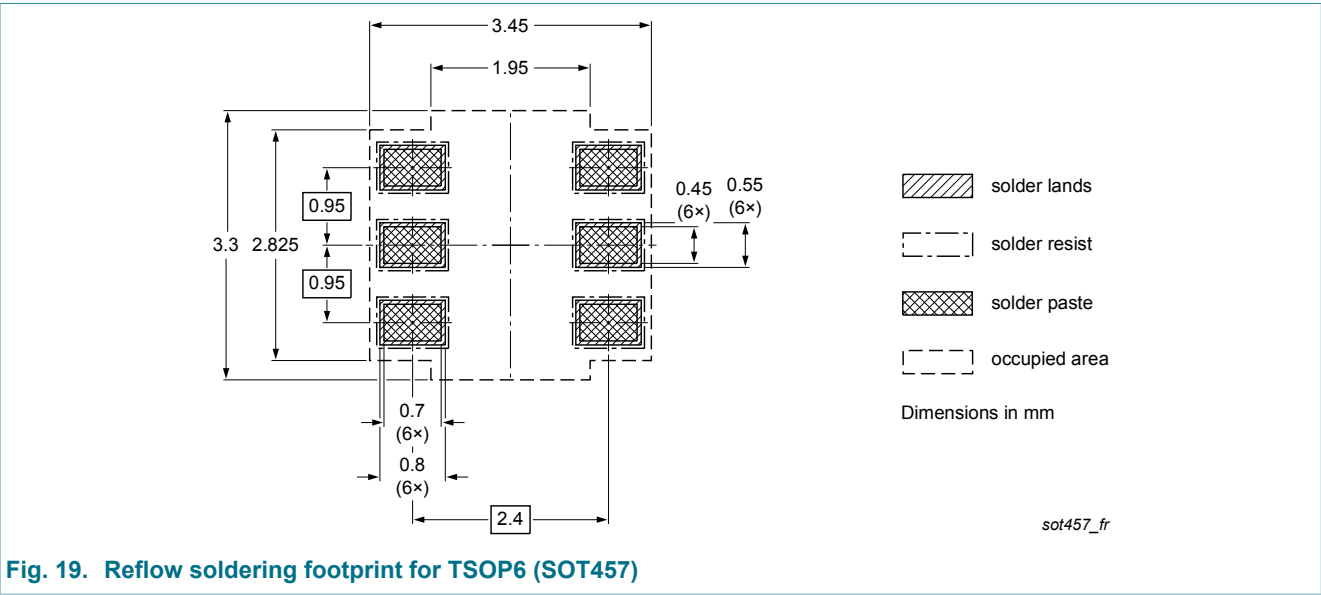


Fig. 17. Duty cycle definition

12. Package outline



13. Soldering



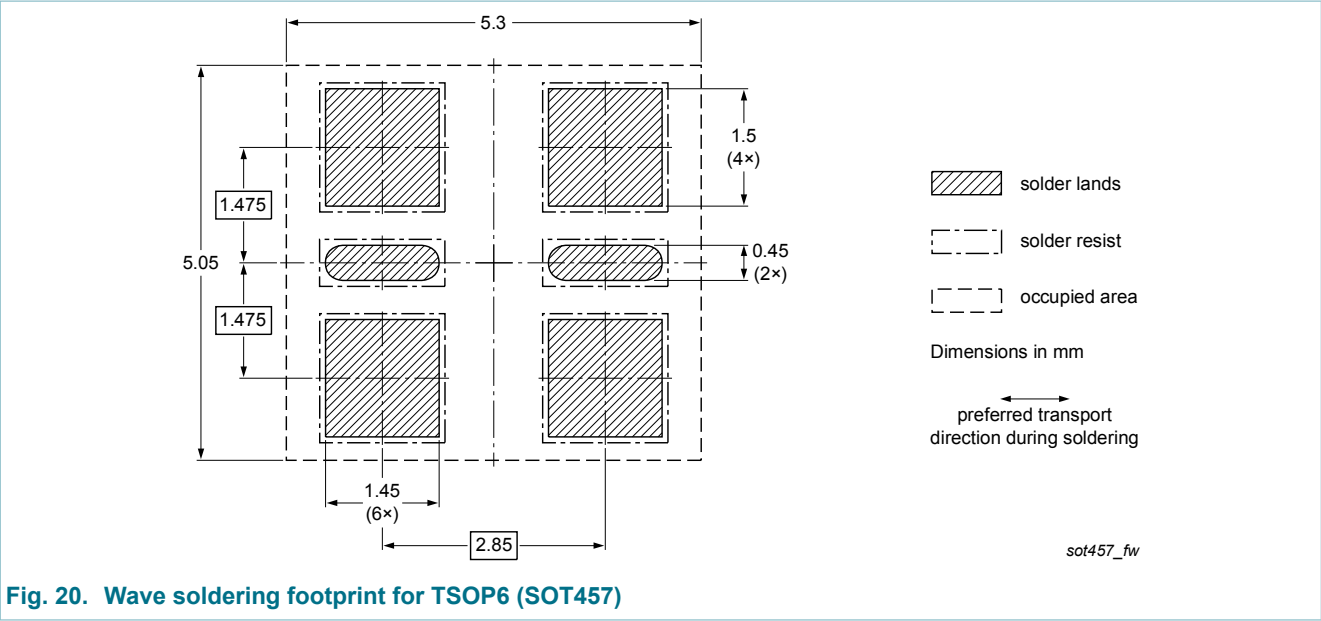


Fig. 20. Wave soldering footprint for TSOP6 (SOT457)

## 14. Revision history

Table 8. Revision history

| Data sheet ID | Release date | Data sheet status  | Change notice | Supersedes |
|---------------|--------------|--------------------|---------------|------------|
| PMN40ENE v.1  | 20160526     | Product data sheet | -             | -          |

## 15. Legal information

### 15.1 Data sheet status

| Document status [1][2]         | Product status [3] | Definition                                                                            |
|--------------------------------|--------------------|---------------------------------------------------------------------------------------|
| Objective [short] data sheet   | Development        | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification      | This document contains data from the preliminary specification.                       |
| Product [short] data sheet     | Production         | This document contains the product specification.                                     |

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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## 16. Contents

|      |                               |    |
|------|-------------------------------|----|
| 1    | General description .....     | 1  |
| 2    | Features and benefits .....   | 1  |
| 3    | Applications .....            | 1  |
| 4    | Quick reference data .....    | 1  |
| 5    | Pinning information .....     | 2  |
| 6    | Ordering information .....    | 2  |
| 7    | Marking .....                 | 2  |
| 8    | Limiting values .....         | 3  |
| 9    | Thermal characteristics ..... | 5  |
| 10   | Characteristics .....         | 7  |
| 11   | Test information .....        | 10 |
| 12   | Package outline .....         | 11 |
| 13   | Soldering .....               | 11 |
| 14   | Revision history .....        | 13 |
| 15   | Legal information .....       | 14 |
| 15.1 | Data sheet status .....       | 14 |
| 15.2 | Definitions .....             | 14 |
| 15.3 | Disclaimers .....             | 14 |
| 15.4 | Trademarks .....              | 15 |

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